



SANYO Semiconductors

## DATA SHEET

# TIG032TS

 — N-Channel IGBT  
**Light-Controlling Flash Applications**

## Features

- Low-saturation voltage.
- Low voltage drive (2.5V).
- Enhancement type.
- Built-in Gate-to-Emitter protection diode.
- Mounting Height 1.1mm, Mounting Area 19.2mm<sup>2</sup>.
- dv / dt guarantee.\*

## Specifications

### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Emitter Voltage	V <sub>CES</sub>		400	V
Gate-to-Emitter Voltage (DC)	V <sub>GES</sub>		±6	V
Gate-to-Emitter Voltage (Pulse)	V <sub>GES</sub>	PW≤1ms	±8	V
Collector Current (Pulse)	I <sub>CP1</sub>	PW≤500μs, duty cycle≤0.5%, C <sub>M</sub> =400μF, V <sub>GE</sub> =2.5V	150	A
	I <sub>CP2</sub>	PW≤500μs, duty cycle≤0.5%, C <sub>M</sub> =400μF, V <sub>GE</sub> =4V	180	A
Maximum Collector-to-Emitter dv / dt	dV <sub>CE</sub> / dt	V <sub>CE</sub> ≤320V, starting T <sub>ch</sub> =25°C	400	V / μs
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-40 to +150	°C

### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Breakdown Voltage	V <sub>(BR)CES</sub>	I <sub>C</sub> =2mA, V <sub>GE</sub> =0V	400			V
Collector-to-Emitter Cutoff Current	I <sub>CES</sub>	V <sub>CE</sub> =320V, V <sub>GE</sub> =0V			10	μA
Gate-to-Emitter Leakage Current	I <sub>GES</sub>	V <sub>GE</sub> =±6V, V <sub>CE</sub> =0V			±10	μA

Marking : G032

Continued on next page.

\* : Conduct 100% screening of dv / dt (slope of collector voltage at the time of turn-off) by dv / dt&gt;400V/μs.

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SANYO Semiconductor Co., Ltd.

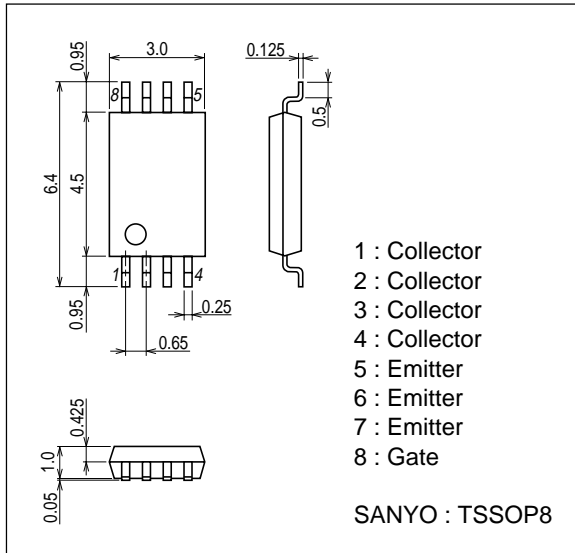
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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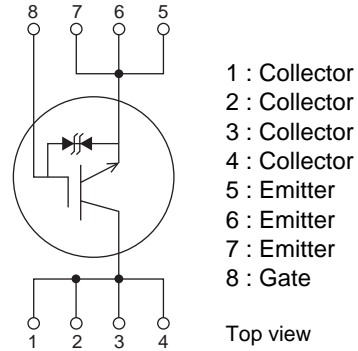
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gate-to-Emitter Threshold Voltage	$V_{GE(off)}$	$V_{CE}=10V, I_C=1mA$	0.4		1.0	V
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)1}$	$I_C=150A, V_{GE}=2.5V$		3.4	4.8	V
	$V_{CE(sat)2}$	$I_C=180A, V_{GE}=4V$		3.3	4.7	V
Input Capacitance	$C_{ies}$	$V_{CE}=10V, f=1MHz$		5100		pF
Output Capacitance	$C_{oes}$	$V_{CE}=10V, f=1MHz$		59		pF
Reverse Transfer Capacitance	$C_{res}$	$V_{CE}=10V, f=1MHz$		43		pF

**Package Dimensions**

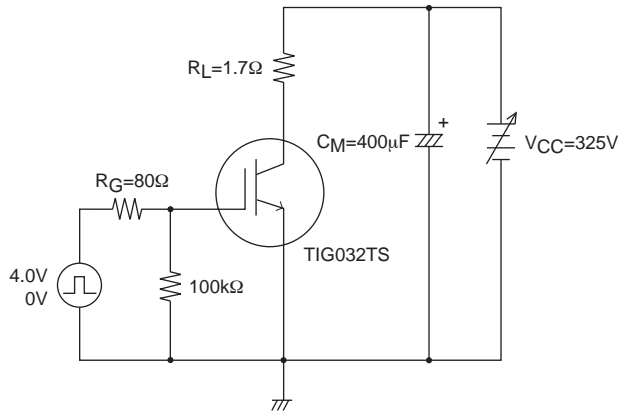
unit : mm (typ)  
7006A-007



**Electrical Connection**

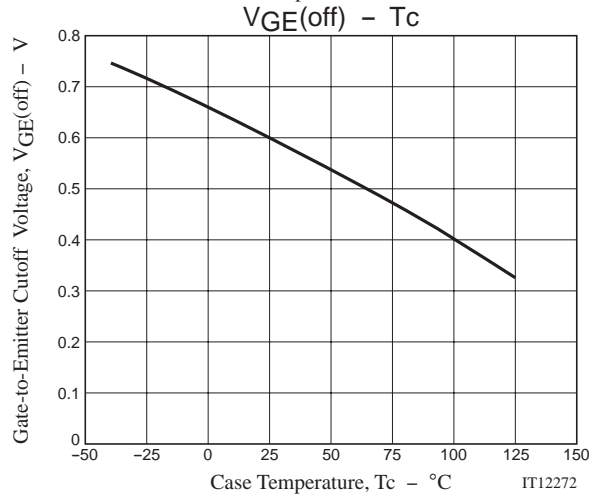
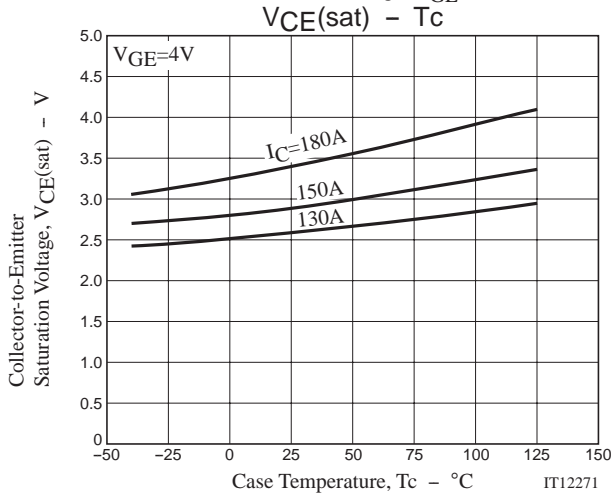
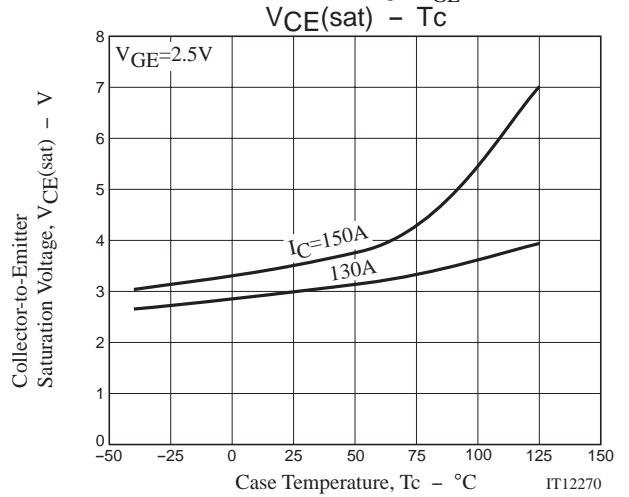
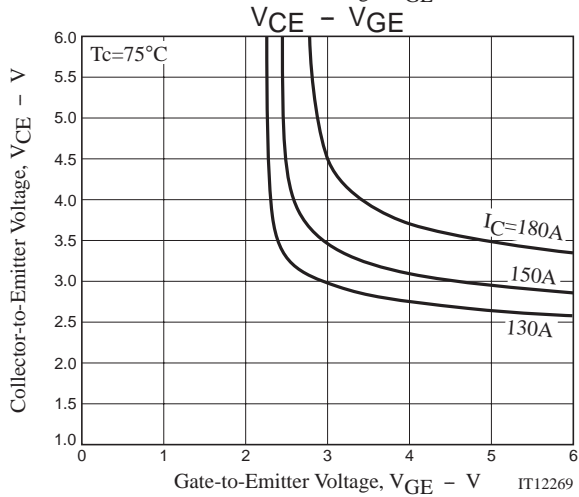
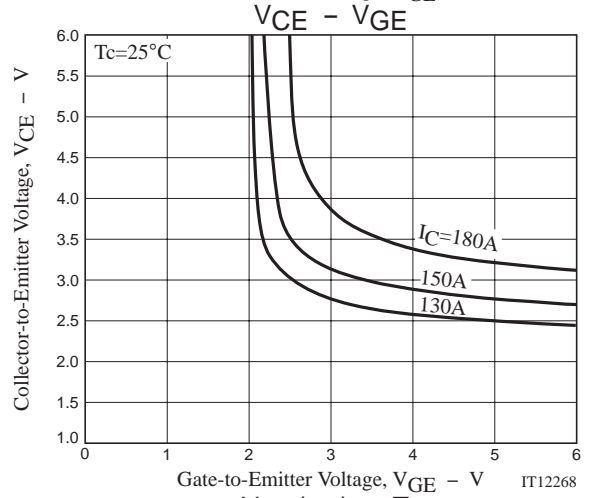
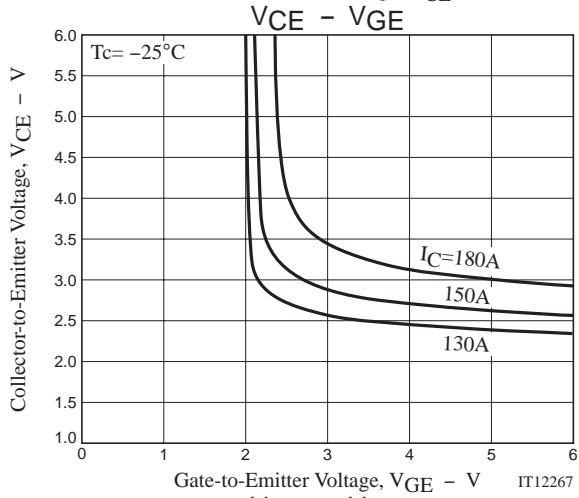
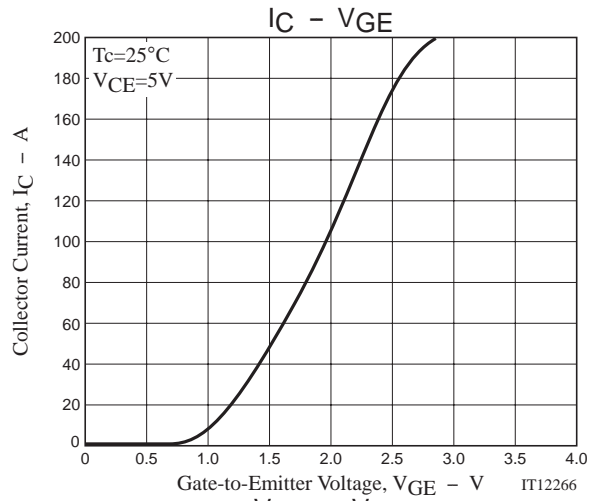
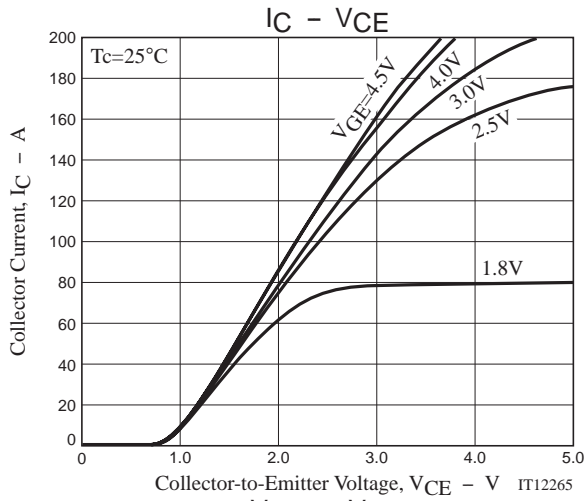


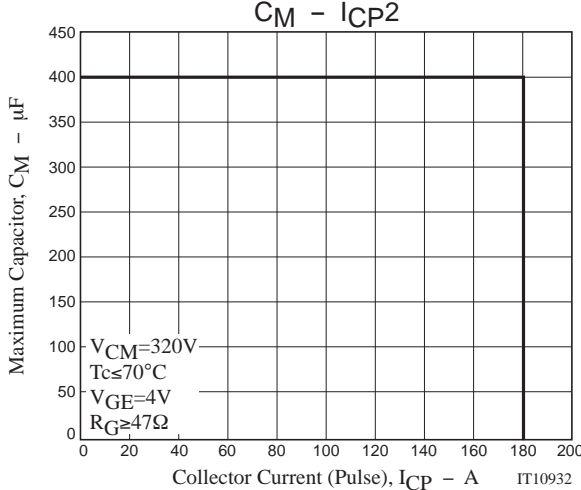
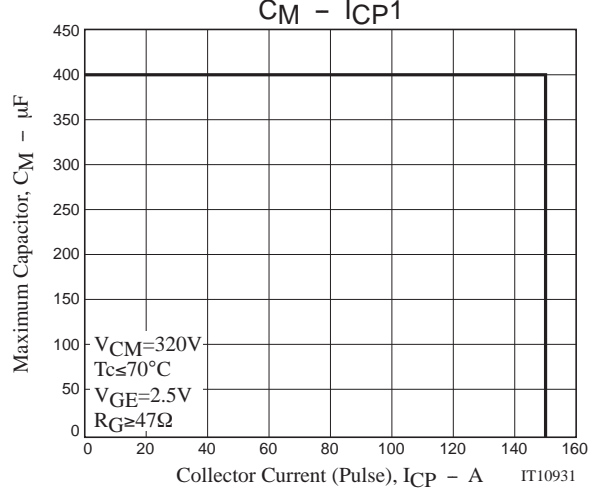
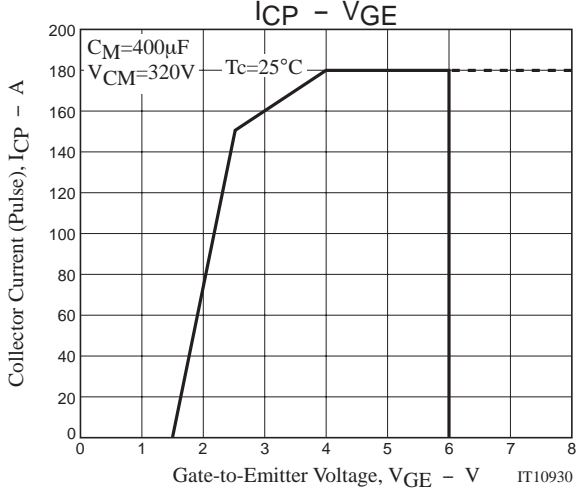
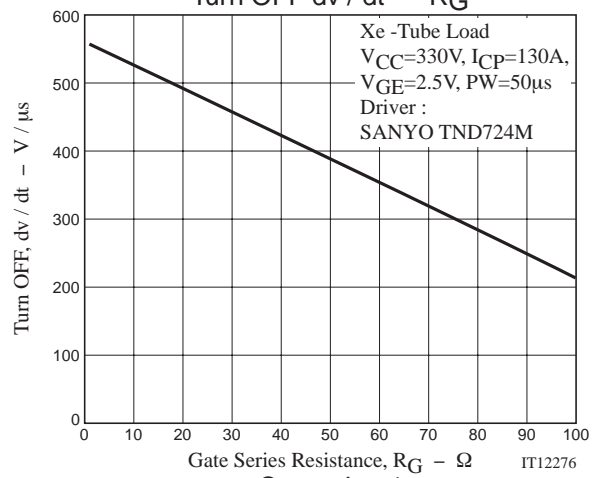
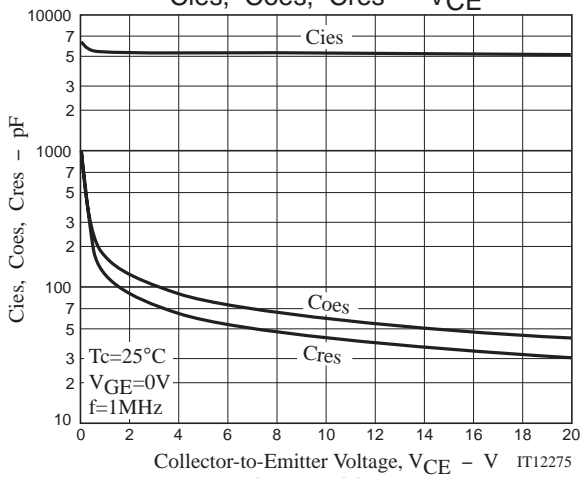
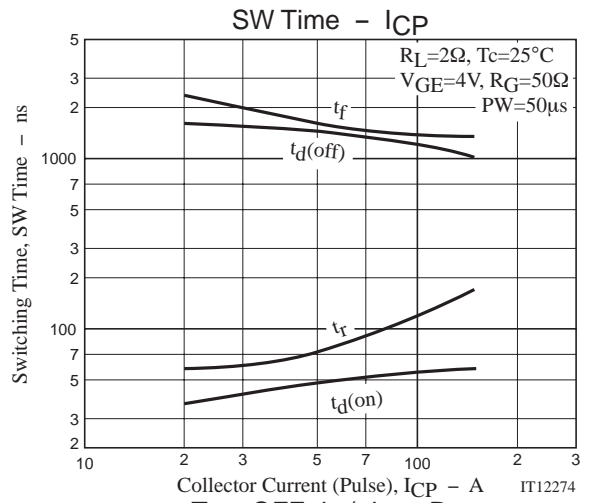
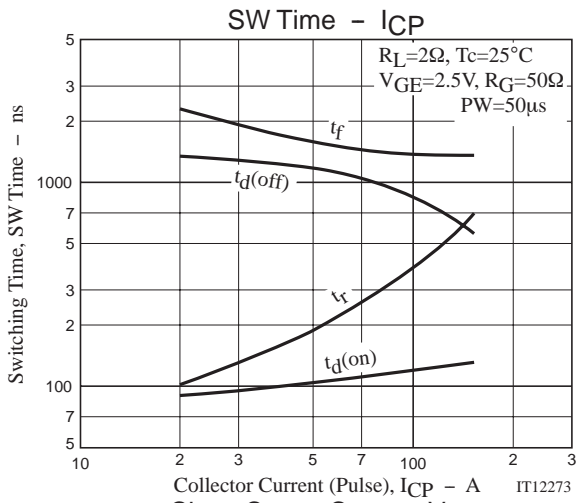
**Large Current R Load Screening Circuit**



Note1. Gate Series Resistance  $R_G \geq 47\Omega$  is recommended for protection purpose at the time of turn OFF. However, if  $dv/dt \leq 400V/\mu s$  is satisfied at customer's actual set evaluation,  $R_G < 47\Omega$  can also be used.

Note2. The collector voltage gradient  $dv/dt$  must be smaller than  $400V/\mu s$  to protect the device when it is turned off.





Note : TIG032TS has protection diode between gate and emitter but handling it requires sufficient care to be taken.

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